AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraph on page 4, beginning at line 6 as follows:

According to another embodiment of the present invention, the passivation process is separated into two independent steps. The first step: a first passivating gas suitable for passivating the PMOS transistors 110 (e.g., H_2 or N_2) is introduced into a chamber 200 under a high pressure (see FIG. 2) and then a semiconductor device 100 is heated to a temperature for a period sufficient to passivate the PMOS transistors 110. The second Step, a second gas suitable for passivating the NMOS transistors 120 (e.g., H_2O or $NH_3[[O]]$) is introduced into the chamber 200 maintained at a high pressure (see FIG.3)and then the semiconductor device 100 is heated to a temperature for a period sufficient to passivate the NMOS transistors 120. Alternatively, the first passivating gas can be drained out of the chamber 200 by introducing the second passivating gas into the chamber 200 such that the NMOS transistor 120 is passivated with only the second passivating gas (see FIG. 4). Since the passivation of the PMOS and NMOS transistors 110, 120 is conducted in an independent manner as described above, the process parameters can be optimized for the NMOS transistors120 and PMOS transistors110 respectively. The PMOS transistors 110 and the NMOS transistors have substantially uniform threshold voltage and the threshold voltage difference between PMOS transistors110 and NMOS transistors 120 was kept at most two volts.

Abstract:

Please replace the current Abstract with the following replacement/new Abstract

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